

Listing of Claims:

This listing of claims replaces all prior versions and listings of claims in the application.

1. (Currently Amended) A semiconductor device ~~comprising~~ comprising: a first electrode of a metal, a ferroelectric film containing Ti formed above the first electrode, and a second electrode of a metal formed above the ferroelectric film, at least one of the first electrode and the second electrode being an electrode of a base metal, the semiconductor device further comprising an intermediate layer of perovskite crystal structure formed between the electrode of the base metal and the ferroelectric film, materials of the intermediate layer being different from materials of the first electrode, the second electrode and the ferroelectric film, the intermediate layer containing Ti.

2. (Original) A semiconductor device according to claim 1, wherein the intermediate layer is BaTiO₃ layer, SrTiO₃ layer, or CaTiO₃ layer.

3. (Original) A semiconductor device according to claim 2, wherein the intermediate layer further contains at least any element of Ca, Sr, Tl, Pb, Bi, rare earth element, Nb, Ta, W, Mo, Fe, Co, Cr, and Zr.

4-6. (Canceled)

7. (Previously Presented) A semiconductor device according to claim 1, wherein the base metal is Ni, Cu or Cr.

8. (Previously Presented) A semiconductor device according to claim 2, wherein the base metal is Ni, Cu or Cr.

9. (Previously Presented) A semiconductor device according to claim 3, wherein the base metal is Ni, Cu or Cr.

10. (Original) A semiconductor device according to claim 1, wherein the ferroelectric film is lead-based oxide ferroelectric film.

11. (Original) A semiconductor device according to claim 10, wherein the lead-based oxide ferroelectric film is $\text{PbZr}_x\text{Ti}_{1-x}\text{O}_3$ film.

12. (Original) A semiconductor device according to claim 11, wherein the $\text{PbZr}_x\text{Ti}_{1-x}\text{O}_3$ film further contains at least any element of La, Sr and Ca.

13. (Currently Amended) A semiconductor device according to claim 1, wherein the ferroelectric film is $(\text{AO})_2(\text{B}_{Y-1}\text{C}_Y\text{O}_{3Y+1})$ film wherein A is at least any element of Tl, Pb, Bi and rare earth element; B is at least any element of Bi, Pb, Ca, Sr and Ba; C is ~~at least any element of Tl, Nb, Ta, W, Mo, Fe, Co, Cr and Zr~~; and Y is any of 2, 3, 4 and 5.

14. (Original) A semiconductor device according to claim 13, wherein the ferroelectric film is bismuth layer structure ferroelectric film.

15. (Currently Amended) A semiconductor device according to claim 14, wherein the bismuth layer structure ferroelectric film is ~~SrBi₂Ta₂O₉ film~~, Bi₂Ba₂Ti₃O₁₂ film or Bi₂Ca₃Ti₄O₁₅ film.

16. (Currently Amended) A semiconductor device comprising a capacitor including a first electrode of a metal, a ferroelectric film containing Ti formed above the first electrode, and a second electrode of a metal formed above the ferroelectric ~~film~~; film, at least one of the first electrode and the second electrode being an electrode of a base ~~metal~~; metal; and a transistor connected to the first electrode or the second electrode, the semiconductor device further comprising

an intermediate layer of perovskite crystal structure formed between the electrode of the base metal and the ferroelectric film, materials of the intermediate layer being different from materials of the first electrode, the second electrode and the ferroelectric film, the intermediate layer containing Ti.

17. (Original) A method for fabricating a semiconductor device comprising the step of forming a first electrode, the step of forming a ferroelectric film above the first electrode, and the step of forming a second electrode above the ferroelectric film, further comprising

the step of forming an intermediate layer which is crystallizable into perovskite structure after the step of forming the first electrode and before the step of forming the ferroelectric film and/or after the step of forming the ferroelectric film and before the step of forming the second electrode.

18. (Original) A method for fabricating a semiconductor device according to claim 17, wherein in the step of forming the intermediate layer, the intermediate layer is formed in an inert atmosphere.

19. (Original) A method for fabricating a semiconductor device according to claim 17, wherein the intermediate layer and the ferroelectric film are formed without exposed to ambient atmosphere.